

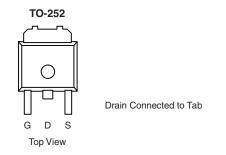
N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)	
250	0.165 at V _{GS} = 10 V	17	

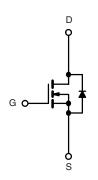
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature





Ordering Information: SUD17N25-165-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$	o°C, unless othe	rwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	250	- V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _{.I} = 175 °C) ^b	$T_C = 25 ^{\circ}C$ $T_C = 125 ^{\circ}C$	- I _D	17		
Continuous Drain Current (1 _J = 175 °C)	T _C = 125 °C		9.8		
Pulsed Drain Current		I _{DM}	20	А	
Continuous Source Current (Diode Conduction)		I _S	17		
Single Pulse Avalanche Current		I _{AS}	5		
Single Pulse Avalanche Energy L = 0.1 mH		E _{AS}	1.25	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	136 ^b	W	
Maximum Power Dissipation	T _A = 25 °C	' D	3 ^a		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Location to Australia	t ≤ 10 sec	R _{thJA}	15	18	°C/W
Junction-to-Ambient ^a	Steady State		40	50	
Junction-to-Case (Drain)	·	R _{thJC}	0.85	1.1	

Notes:

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. See SOA curve for voltage derating.

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Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit	
Static	•						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.5		4.0		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V, T _J = 125 °C			50	μΑ	
		$V_{DS} = 250 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 175 ^{\circ}\text{C}$			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}$	17			Α	
Drain-Source On-State Resistance ^b		V _{GS} = 10 V, I _D = 14 A		0.131	0.165		
	r _{DS(on)}	V _{GS} = 10 V, I _D = 14 A, T _J = 125 °C			0.347	Ω	
		V _{GS} = 10 V, I _D = 14 A, T _J = 175 °C			0.462		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 17 A		36		S	
Dynamic ^a							
Input Capacitance	C _{iss}			1950		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		160			
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Q_g			30	42		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 125 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 17 \text{ A}$		10		nC	
Gate-Drain Charge ^c	Q_{gd}			10			
Gate Resistance	R_{g}			1.6		Ω	
Turn-On Delay Time ^c	t _{d(on)}			15	25		
Rise Time ^c	t _r	$V_{DD} = 125 \text{ V}, R_1 = 7.35 \Omega$		130	195	ns	
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong 17 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 2.5 \Omega$		30	45		
Fall Time ^c	t _f			100	150		
Source-Drain Diode Ratings and Cha	racteristics	(T _C = 25 °C)		1	<u> </u>		
Pulsed Current	I _{SM}				20	Α	
Diode Forward Voltage ^b	V_{SD}	I _F = 17 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 17 A, di/dt = 100 A/μs		115	175	ns	

Notes:

- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. Independent of operating temperature.

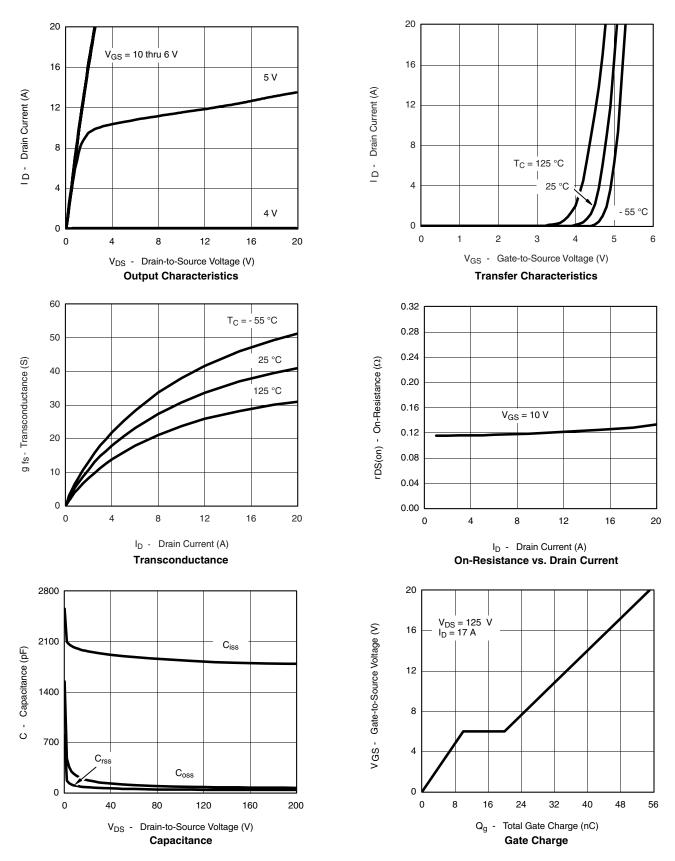
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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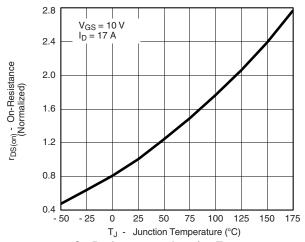
TYPICAL CHARACTERISTICS 25 °C unless noted





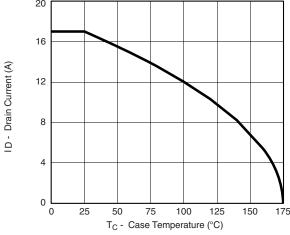
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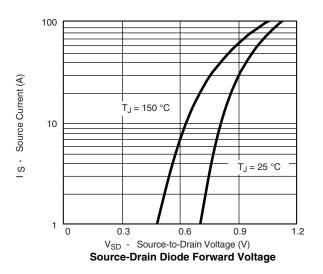


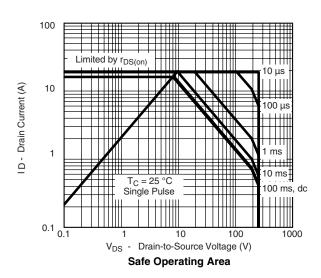
On-Resistance vs. Junction Temperature

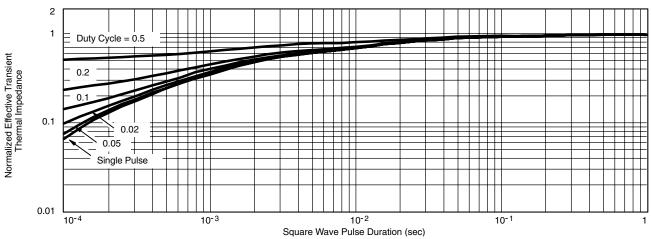
THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature







Normalized Thermal Transient Impedance, Junction-to-Case

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